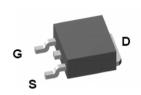




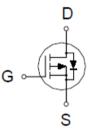
### **P-Channel Enhancement Mode MOSFET**

#### **PRODUCT SUMMARY**

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub>	I <sub>D</sub>
-30V	45m $\Omega$ @V <sub>GS</sub> = −10V	-12A



TO-252



### **ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub> = 25 °C Unless Otherwise Noted)**

PARAMETERS/TEST C	SYMBOL	LIMITS	UNITS		
Drain-Source Voltage	$V_{DS}$	-30	1/		
Gate-Source Voltage	$V_{GS}$	±20	ľ		
Continuous Drain Current	T <sub>C</sub> = 25 °C	1	-12		
Continuous Diam Current	T <sub>C</sub> = 100 °C	- I <sub>D</sub>	-10	A	
Pulsed Drain Current <sup>1</sup>		I <sub>DM</sub>	-30	<b>1</b> ^	
Avalanche Current		I <sub>AS</sub>	-29		
Avalanche Energy	L = 0.1mH	E <sub>AS</sub>	42	mJ	
Dower Discipation	T <sub>C</sub> = 25 °C	P <sub>D</sub>	48	W	
Power Dissipation	T <sub>C</sub> = 100 °C	' D	20		
Operating Junction & Storage Temperature Range		$T_J, T_STG$	-55 to 150	°C	

#### THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Case	$R_{ heta JC}$		3	°C / W
Junction-to-Ambient	$R_{ heta JA}$		75	

<sup>&</sup>lt;sup>1</sup>Pulse width limited by maximum junction temperature.





# **P-Channel Enhancement Mode MOSFET**

**ELECTRICAL CHARACTERISTICS (T<sub>1</sub> = 25 °C, Unless Otherwise Noted)** 

PARAMETER	CVMDOL	TEST CONDITIONS		LIMITS			
PARAMETER	SYMBOL TEST CONDITIONS		MIN	TYP	MAX	UNIT	
		STATIC	8				
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-30			V	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, \ I_D = -250 \mu A$	-1	-1.5	-3	٧	
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0V, V_{GS} = \pm 20V$			±250	nA	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = -24V, V_{GS} = 0V$ $V_{DS} = -20V, V_{GS} = 0V, T_{J} = 125 \text{ °C}$			-1 -10	μΑ	
On-State Drain Current <sup>1</sup>	I <sub>D(ON)</sub>	$V_{DS} = -5V$ , $V_{GS} = -10V$	-30			Α	
Drain-Source On-State		$V_{GS} = -4.5V, I_D = -10A$		60	75		
Resistance <sup>1</sup>	R <sub>DS(ON)</sub>	$V_{GS} = -10V, I_D = -12A$		37	45	$\mathbf{m}\Omega$	
Forward Transconductance <sup>1</sup>	g <sub>fs</sub>	$V_{DS} = -10V, I_{D} = -12A$		16		S	
		DYNAMIC					
Input Capacitance	C <sub>iss</sub>			530			
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0V$ , $V_{DS} = -15V$ , $f = 1MHz$		135		pF	
Reverse Transfer Capacitance	$C_{rss}$			70			
Total Gate Charge <sup>2</sup>	$Q_g$	V = 0.5V V = -10V		10			
Gate-Source Charge <sup>2</sup>	$Q_gs$	$V_{DS} = 0.5V_{(BR)DSS}, V_{GS} = -10V,$ $I_{D} = -12A$		2.2		nC	
Gate-Drain Charge <sup>2</sup>	$Q_{gd}$	-U - 12/1		2			
Turn-On Delay Time <sup>2</sup>	t <sub>d(on)</sub>			5.7			
Rise Time <sup>2</sup>	t <sub>r</sub>	$V_{DS}$ = -15V, RL = 1 $\Omega$		10		nS	
Turn-Off Delay Time <sup>2</sup>	$t_{d(off)}$	$I_{D}\cong$ -1A, $V_{GS}$ = -10V, $R_{GS}$ = 6 $\Omega$		18		110	
Fall Time <sup>2</sup>	t <sub>f</sub>			5			
SOURCE-DRA	AIN DIODE	RATINGS AND CHARACTERISTICS (	$T_J = 25$	°C)			
Continuous Current	I <sub>S</sub>				-12	Α	
Forward Voltage <sup>1</sup>	$V_{SD}$	$I_F = -1A$ , $V_{GS} = 0V$			-1.2	V	
Reverse Recovery Time	t <sub>rr</sub>	IF = -5A, dIF/dt = 100A / μS		15.5		nS	
Reverse Recovery Charge	$Q_{rr}$	π = -5Α, αιτ/αι = 100Α / μ5		7.9		nC	
						_	

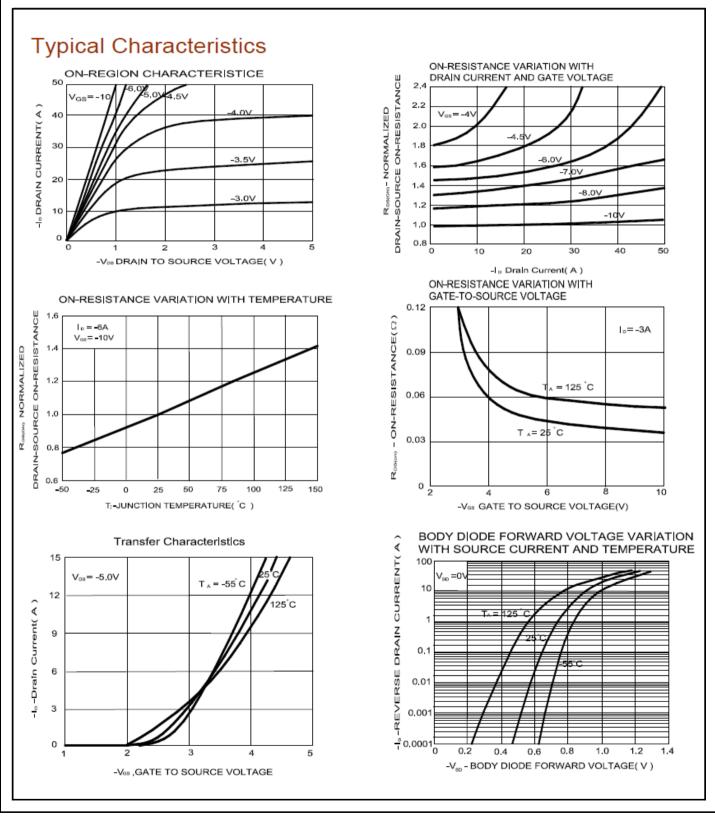
<sup>&</sup>lt;sup>1</sup>Pulse test : Pulse Width  $\leq$  300 µsec, Duty Cycle  $\leq$  2%.

<sup>&</sup>lt;sup>2</sup>Independent of operating temperature.





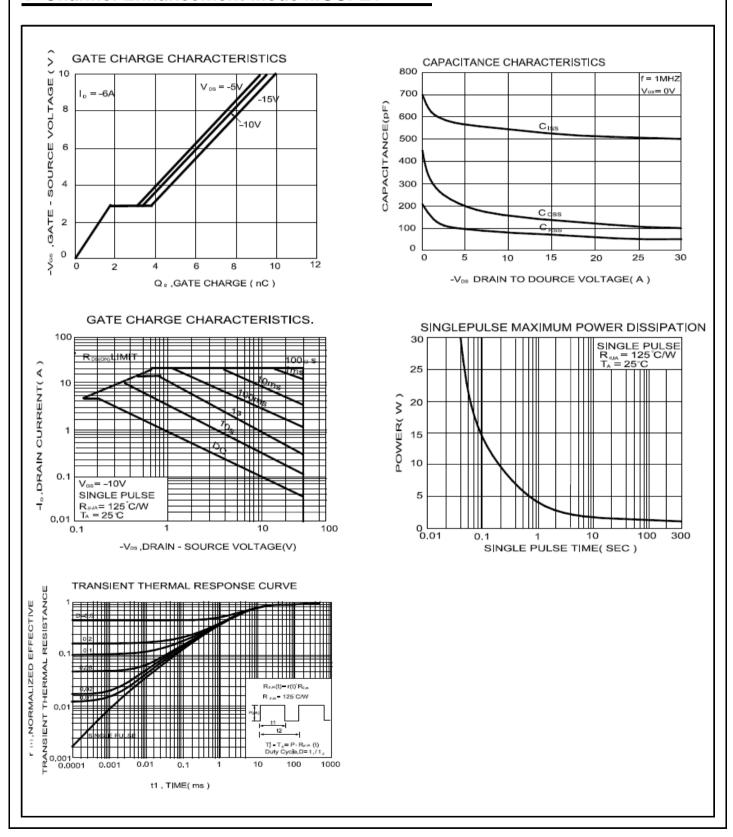
#### **P-Channel Enhancement Mode MOSFET**







#### **P-Channel Enhancement Mode MOSFET**





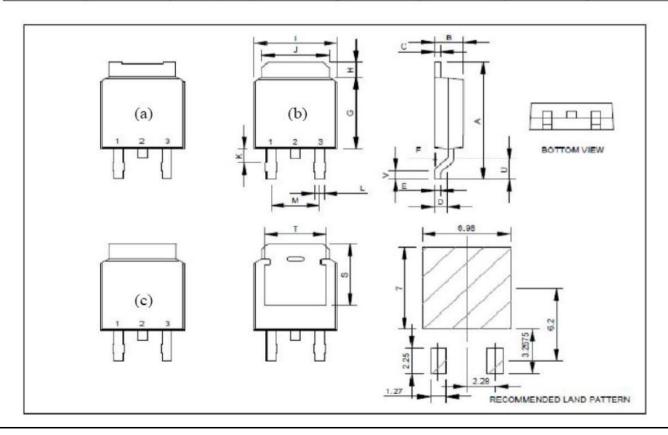


# **P-Channel Enhancement Mode MOSFET**

#### Package Dimension

# TO-252 (DPAK) MECHANICAL DATA

Dimension	mm				mm		
	Min.	Тур.	Max.	Dimension	Min.	Typ.	Max.
Α	8.9	10	10.41	J	4.8		5.64
В	2.1	2.2	2.5	K	0.15		1.49
С	0.4	0.5	0.61	L	0.4	0.76	0.91
D	0.82	1.2	1.5	M	4.2	4.58	5
E	0.35	0.5	0.65	s	4.57	5.1	5.52
F	0		0.2	Т	3.81	4.75	5.24
G	5.3	6.1	6.3	U	1.4		1.78
Н	0.5		1.7	V	0.55	1.25	1.7
L	6.3	6.5	6.8				



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